L Number	Hits	Search Text	DB	Time stamp
1	29	silicon adj nitirde	USPAT;	2004/06/22 22:51
			US-PGPUB	
2	75787	silicon adj nitride	USPAT;	2004/06/22 22:51
			US-PGPUB	
3	5140	"Si.sub.3N.sub.4"	USPAT;	2004/06/22 22:51
			US-PGPUB	
4	1184	plasma adj (nitrid\$5 or nitrification or nitration)	USPAT;	2004/06/22 22:53
			US-PGPUB	
5	88035	microwave\$1	USPAT;	2004/06/22 22:53
			US-PGPUB	
6	103196	chemical adj vapor adj deposit\$3 or CVD	USPAT;	2004/06/22 22:54
			US-PGPUB	
7	2524	atomic adj layer adj deposit\$3 or ALD	USPAT;	2004/06/22 22:54
			US-PGPUB	
8	3	((silicon adj nitride) or "Si.sub.3N.sub.4") same (plasma adj (nitrid\$5 or nitrification or	USPAT;	2004/06/22 23:15
		nitration)) same microwave\$1 same ((chemical adj vapor adj deposit\$3 or CVD) or (atomic	US-PGPUB	
		adj layer adj deposit\$3 or ALD))		
9	2	((	USPAT;	2004/06/22 23:04
	_	adj deposit\$3 or CVD)) same microwave\$1	US-PGPUB	
10	0	(conserved) marasy or (smooth adj marasy) same (remete adj misroware) adj (orientada adj	USPAT;	2004/06/22 23:03
		vapor adj deposit\$3 or CVD))	US-PGPUB	
11	215262	plasma	USPAT;	2004/06/22 23:03
			US-PGPUB	
12	11	((	USPAT;	2004/06/22 23:08
		adj deposit\$3 or CVD))	US-PGPUB	
13	618	((silicon adj nitirde) or (silicon adj nitride)) same microwave\$1	USPAT;	2004/06/22 23:08
	•	// III	US-PGPUB	
14	- 9	((	USPAT;	2004/06/22 23:14
		nitration)) same microwave\$1 same ((chemical adj vapor adj deposit\$3 or CVD) or (atomic	US-PGPUB	
45		adj layer adj deposit\$3 or ALD)))		0004/00/00 00 15
15	70	(Company of the property of th	USPAT;	2004/06/22 23:16
		nitration)) same ((chemical adj vapor adj deposit\$3 or CVD) or (atomic adj layer adj	US-PGPUB	
L		deposit\$3 or ALD))		